

MA3S795E

Silicon epitaxial planar type

For switching circuits

■ Features

- Extra-small (SS-mini type) package, allowing high-density mounting
- Optimum for low voltage rectification because of its low V_F ($V_F = 0.3$ V or less at $I_F = 1$ mA)
- Optimum for high-frequency rectification because of its short reverse recovery time (t_{rr})

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|------------------------|-----------|-------------|------------------|
| Reverse voltage (DC) | V_R | 30 | V |
| For switching circuits | V_{RM} | 30 | V |
| Peak forward current | Single | 150 | mA |
| | Double* | | |
| Forward current (DC) | Single | I_F | mA |
| | Double* | | |
| Junction temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |

Note) * : Value per chip

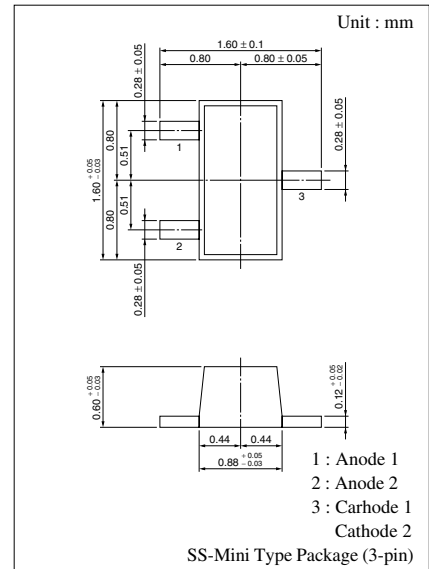
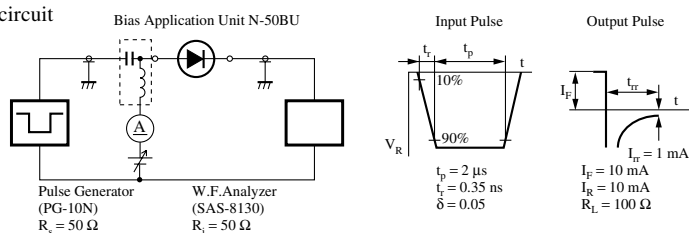
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|------------------------|----------|---|-----|-----|-----|---------------|
| Reverse current (DC) | I_R | $V_R = 30$ V | | | 30 | μA |
| Forward voltage (DC) | V_{F1} | $I_F = 1$ mA | | | 0.3 | V |
| | | $I_F = 30$ mA | | | 1 | V |
| Terminal capacitance | C_t | $V_R = 1$ V, $f = 1$ MHz | | 1.5 | | pF |
| Reverse recovery time* | t_{rr} | $I_F = I_R = 10$ mA $I_{rr} = 1$ mA, $R_L = 100$ Ω | | 1 | | ns |
| Detection efficiency | η | $V_{in} = 3$ V (V_{peak}), $f = 30$ MHz $R_L = 3.9$ k Ω , $C_L = 10$ pF | | 65 | | % |

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 2 000 MHz

3. *: t_{rr} measuring circuit



Marking Symbol: M3D

Internal Connection

